Infineon PowerMos Development within the scope of the ECI Program

ECI Meeting Sept. 2016 Rome

Wolfgang Kuebler Senior Marketing Manager HiRel Products





Project European RH PowerMOS

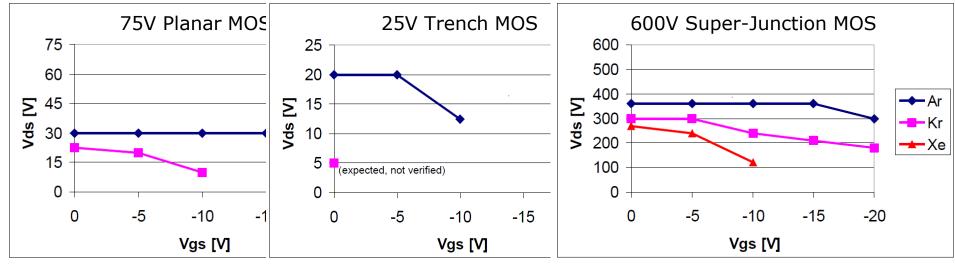
RH PowerMOS Product Range

RH PowerMOS Space Heritage

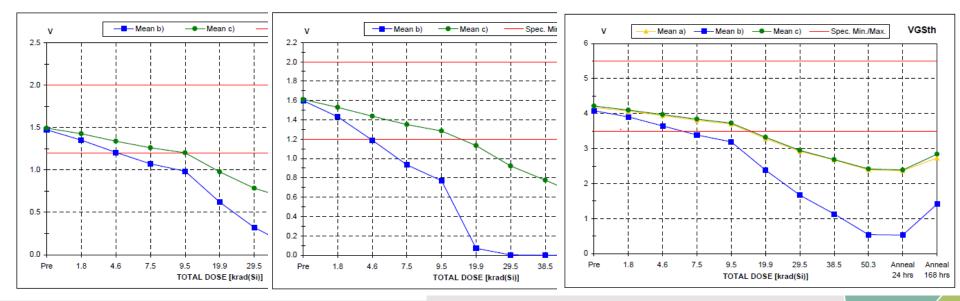


The Project Begnis: Historical Rad Test; SEE and TID Non Rad-Hard Standard Technologies





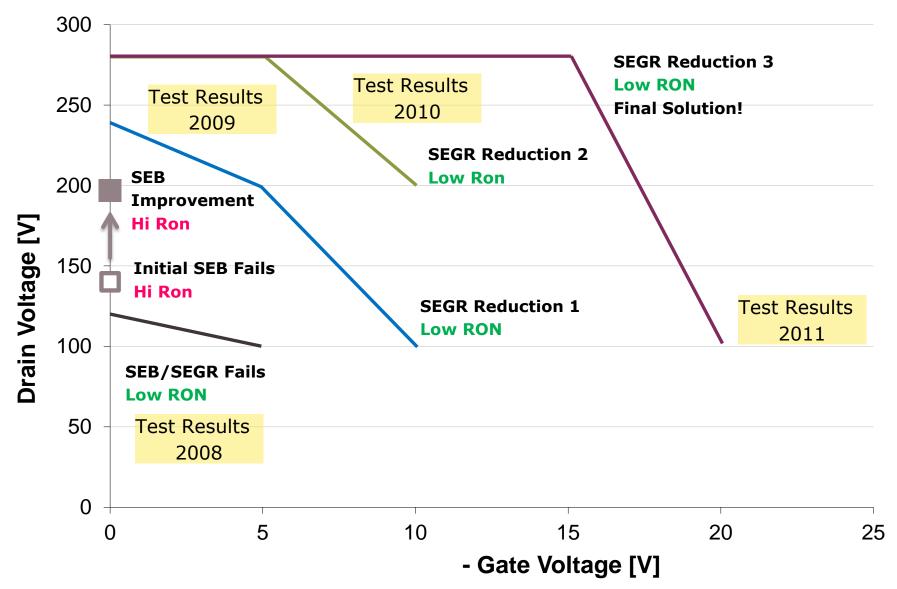
- Ar=LET14MeVcm²/mg; -Kr=LET34MeVcm²/mg; -Xe = LET55MeVcm²/mg



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Radiation Hard PowerMOS SEE hardness development steps (250V)





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Radiation Hard PowerMOS Finally the qualification!



european space agency agence spatiale européenne

Certificate of Qualification No. 319

This is to certify that INFINEON Technologies AG, Neubiberg, Germany has been qualified by ESA for the supply of Transistors, Power, MOSFET, N-Channel, Based on Type BUY**CS*** for use in ESA space programmes, according to ESCC Generic Specification 5000 and associated Detail Specifications 5205/026, 5205/027 and 5205/028 as recommended by the Space Components Steering Board.

This certificate is valid until August 2014.

Head of the Product Assurance and Safety Department

Date 21 August 2012



Radiation Hard PowerMOS Products 250V N-Channel



Drain Voltage [V]

250

200

150

100

0

-5

Radiation-hardened:

- Total Ionization Dose (TID) 100krad
- Single Event Effect (SEE):
 LET 85, Range: 118µm VGS = -10V, VDS = 250V;
 LET 55, Range: 90µm VGS = -15V, VDS = 250V;

Datasheet available at:

WWW.Infineon.com/RadHardMOS

Devices also available as qualified bare die (chip) on request

Туре	ESCC Reference	RDSon max; 25°C	IDC	Umax	Package	ESA QPL
BUY25CS12J-01	5205/026	130mOhm	12A	250V	SMD0.5	yes
BUY25CS54A-01	5205/027	30mOhm	54A	250V	SMD2	yes
BUY25CS12K-01	5205/030/01	130mOhm	12A	250V	TO257AA	yes
BUY25CS45B-01	5205/030/03	50mOhm	45A	250V	TO254AA	yes







-20

-15



SEE Save Operating Area

-10

Gate Voltage [V]

LET55 (Xe @ 90µm) _____ LET85 (Au @ 118µm)

2016-10-06

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Radiation Hard PowerMOS Products 150V N-Channel

Radiation-hardened:

- Total Ionization Dose TID 100krad >
- Single Event Effect (SEE): > LET 73, Range: $253\mu m VGS = -10V$, VDS = 150V; LET 55, Range: $95\mu m VGS = -15V$, VDS = 150V;

Datasheet available at:

WWW.Infineon.com/RadHardMOS

Devices also available as qualified bare die (chip) on request

Туре	ESCC Reference	RDSon max; 25°C	IDC	Uma x	Package	ESA QPL
BUY15CS23J-01	5205/031/01	60mOhm	23A	150V	SMD0.5	yes
BUY15CS57A-01	5205/031/02	11mOhm	57A	150V	SMD2	yes
BUY15CS23K-01	5205/031/03	60mOhm	23A	150V	TO257AA	yes
BUY15CS45B-01	5205/031/04	27mOhm	45A	150V	TO254AA	yes



ESA qualified Device!

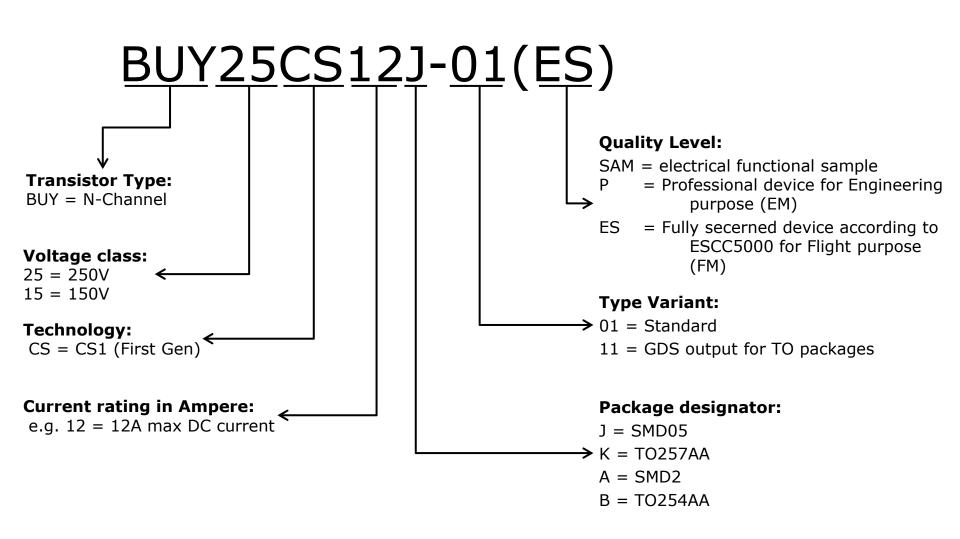






Radiation Hard PowerMOS Nomenclature





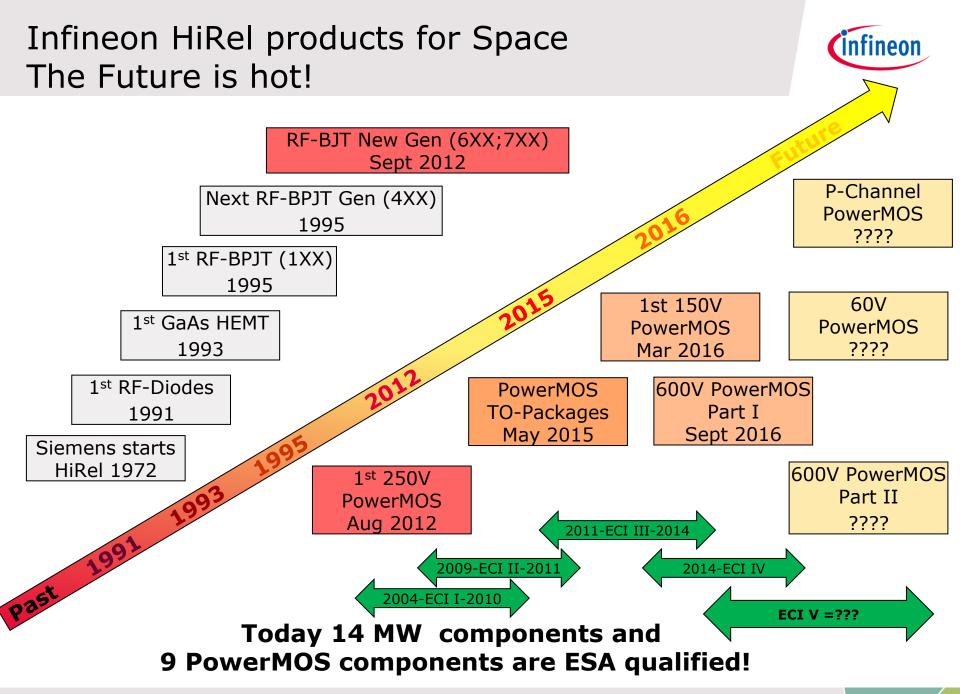
Radiation Hard PowerMOS Space Heritage





JAXA Hayabusa II launched Dec 3. 2014!

PowerMOS included in Mobil Asteroid Surface Scout (Mascot) Regular function tests of RadHardMos running





Infineon HiRel products for Space



In every Project there are ups and downs!



But as a Team we can manage!



Infineon HiRel products for Space

Thank you! For the continuous support!





Part of your life. Part of tomorrow.

